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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK1167, 2SK1168

Silicon N-Channel MOS FET

RENESAS

ADE-208-1253 (Z)
1st. Edition
Mar. 2001

Application

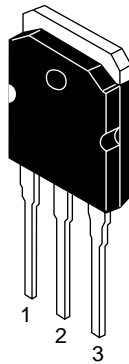
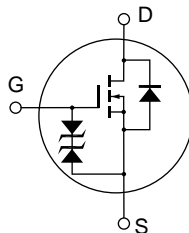
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-3P



1. Gate
2. Drain
(Flange)
3. Source

2SK1167, 2SK1168

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1167	V_{DSS}	450	V
	2SK1168		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	15	A
Drain peak current		$I_{D(pulse)}^{*1}$	60	A
Body to drain diode reverse drain current		I_{DR}	15	A
Channel dissipation		Pch^{*2}	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

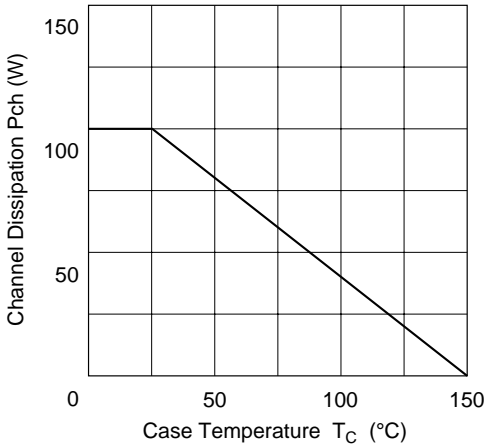
2. Value at $T_C = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

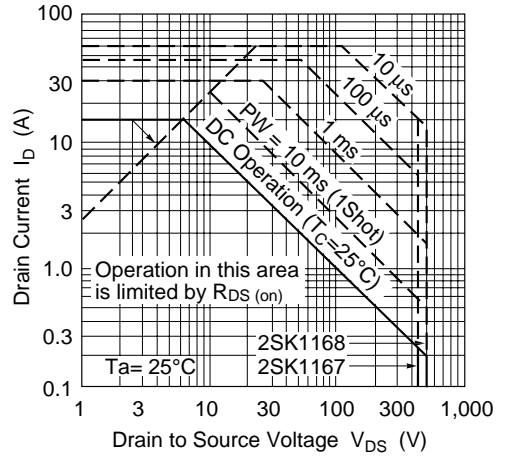
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1167 $V_{(BR)DSS}$ 2SK1168	450 500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK1167 I_{DSS} 2SK1168	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$ $V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1167 $R_{DS(on)}$ 2SK1168	—	0.25 0.30	0.36 0.40	Ω	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	8	13	—	S	$I_D = 8 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	2050	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	600	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	75	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	110	—	ns	$R_L = 3.75 \Omega$
Turn-off delay time	$t_{d(off)}$	—	150	—	ns	
Fall time	t_f	—	70	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 15 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	500	—	ns	$I_F = 15 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

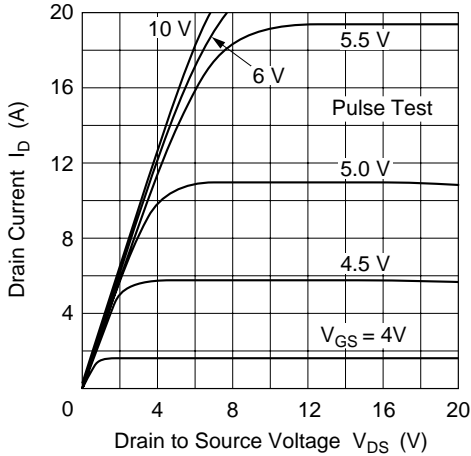
Power vs. Temperature Derating



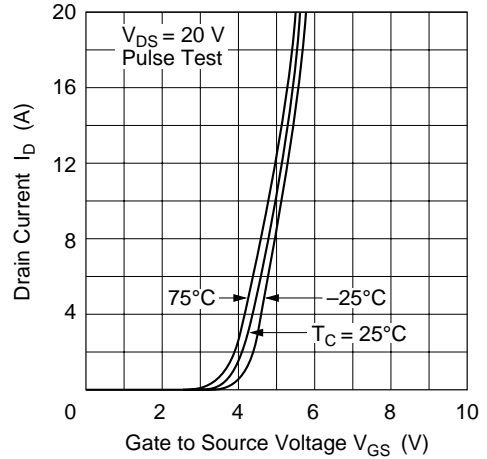
Maximum Safe Operation Area

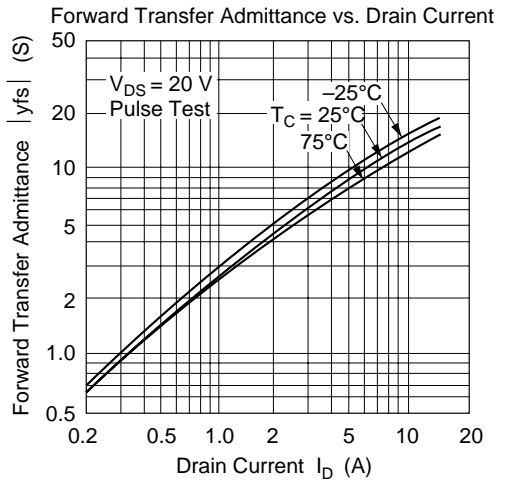
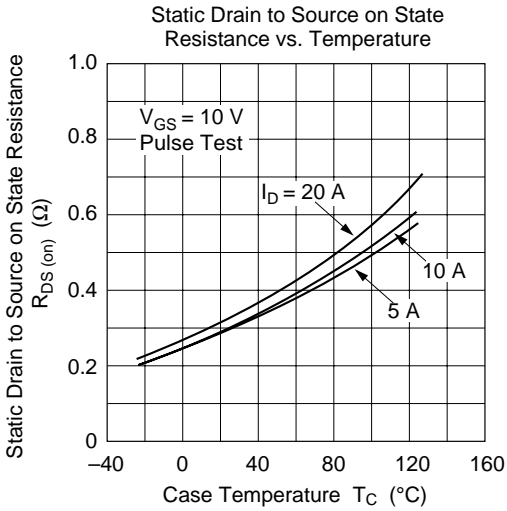
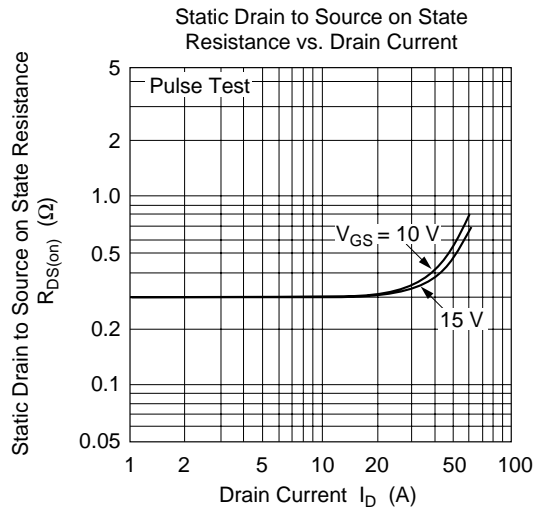
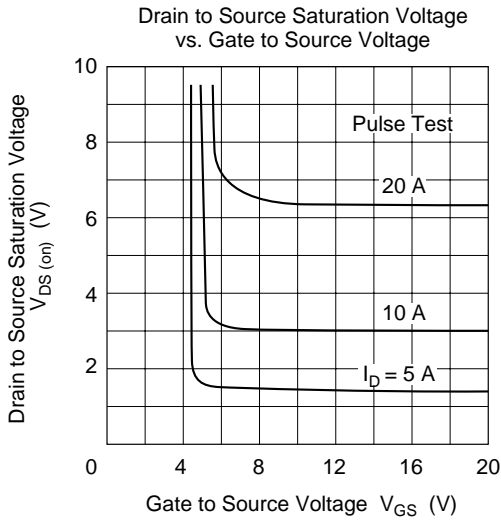


Typical Output Characteristics

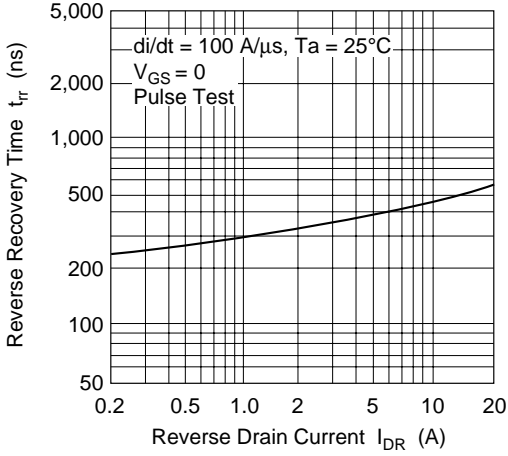


Typical Transfer Characteristics

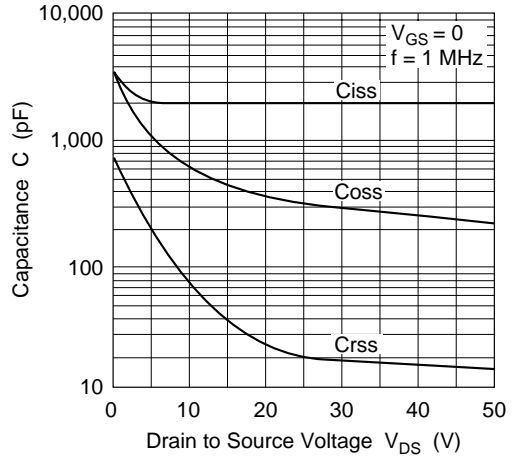




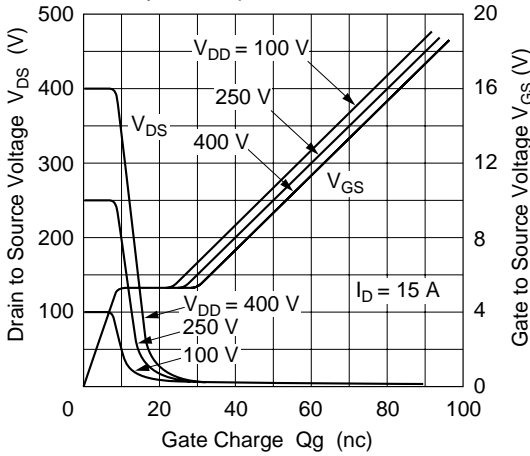
Body to Drain Diode Reverse Recovery Time



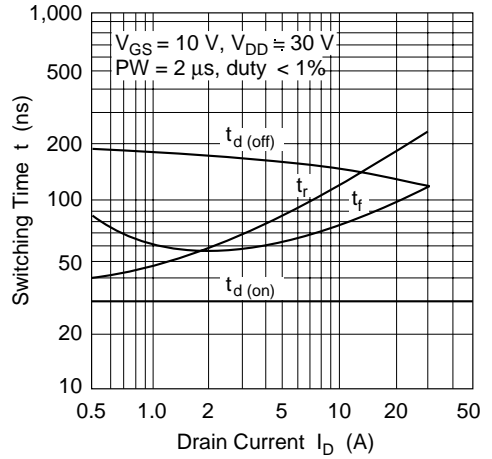
Typical Capacitance vs. Drain to Source Voltage

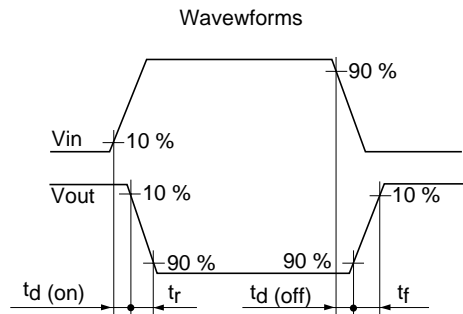
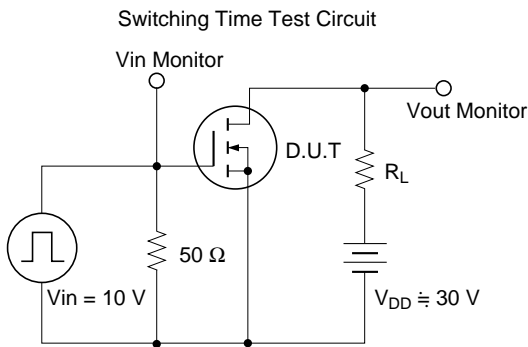
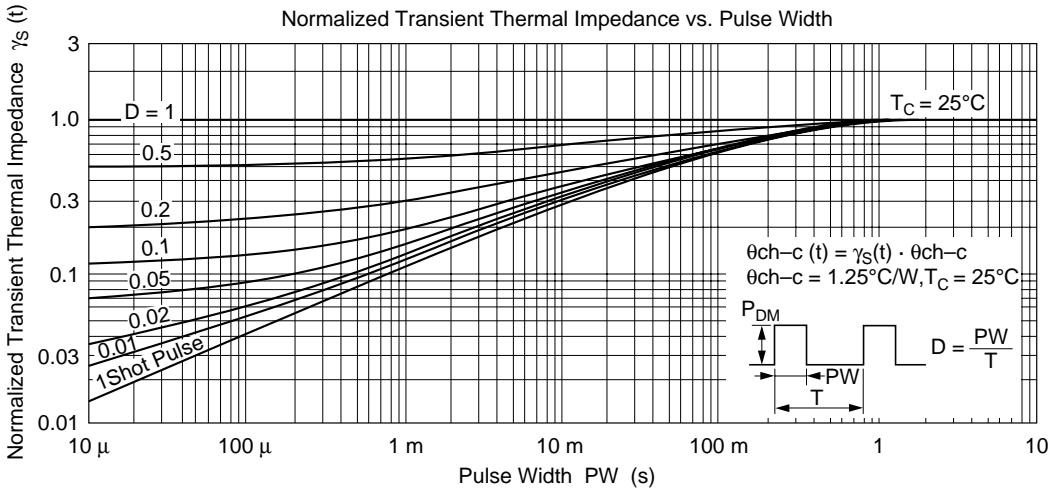
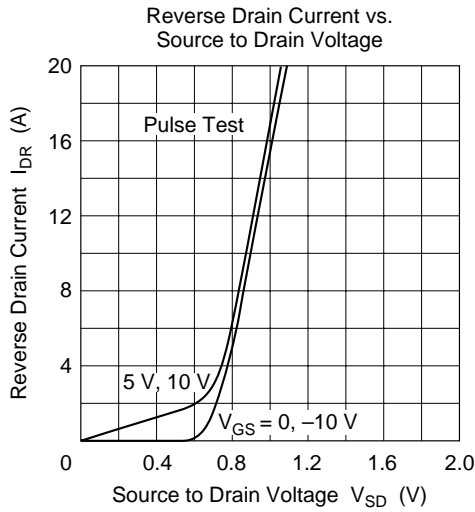


Dynamic Input Characteristics

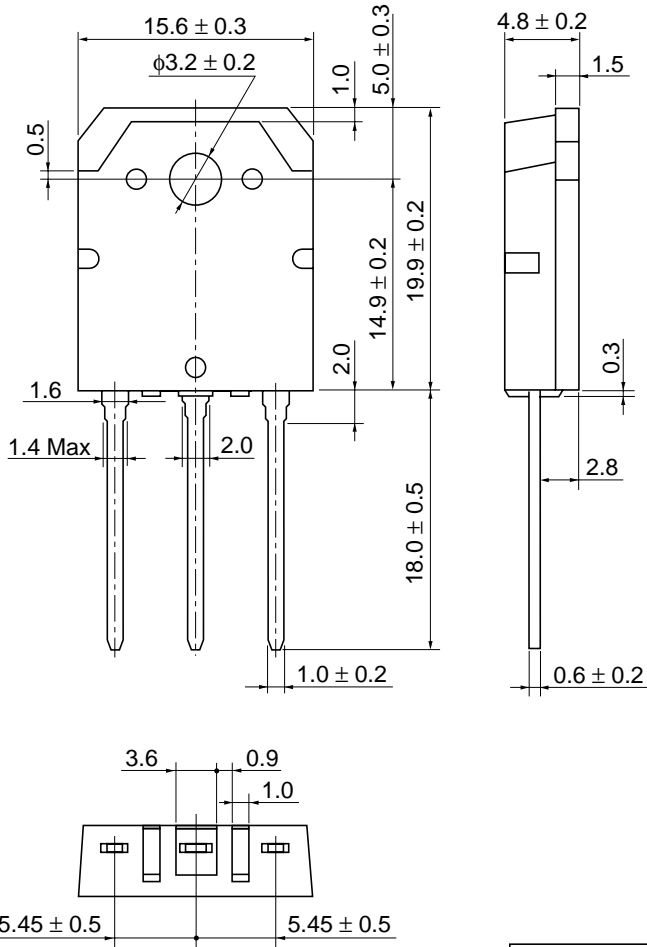


Switching Characteristics



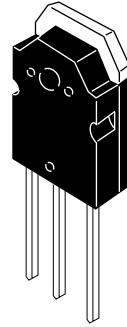


Package Dimensions



As of January, 2001

Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

Cautions

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